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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	1	of	2
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Complete if Known

Application Number	09/375,081
Filing Date	August 16, 1999
First Named Inventor	Fernando Gonzalez
Group Art Unit	2811
Examiner Name	
Attorney Docket Number	MIQ 007 NA

U.S. PATENT DOCUMENTS

Examiner Initials ¹	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
207A		4,213,139		Rao	07/15/1980	
		4,319,263		Rao	03/09/1982	
		4,472,821		Mazin et al.	09/18/1984	
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[illegible]

Examiner
Signature

G. MUNSON

Date
Considered

1 MARCH 2000

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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PTO/SB/08B (10-96)

Approved for use through 10/31/99. OMB 0651-0031

Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary) Sheet 2 of 2				Complete if Known	
				Application Number	09/375,081
				Filing Date	August 16, 1999
				First Named Inventor	Fernando Gonzalez
				Group Art Unit	2811
				Examiner Name	
				Attorney Docket Number	MIO 007 NA

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials [*]	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
27/27		Tiao-yuan Huang, William W. Yao, Russell A. Martin, Alan G. Lewis, Mitsumasa Koyanagi, & John Y. Chen, "A Novel Submicron LDD Transistor with Inverse-T Gate Structure, IDEM 1986, pp. 742-745.	
		I.C. Chen, J. P. Lin, and C. W. Teng, Article from 1990 Symposium on VLSI Technology entitled: "A Highly Reliable 0.3 u N-channel MOSFET Using Poly Spacers", pp. 39-40.	
		Masataka Minami, Yasuo Sawahata, Hiroshi Matsuki and Takahiro Nagano, Article from 1990 Symposium on VLSI Technology entitled: "A High Speed & High Reality MOFSET Utilizing an Auxiliary Gate, p. 41-42.	
		F. -C. Hsu and K. - Y. Chiu, Article from IEEE Electron Device Letters, Vol. EDL-5, No. 5, entitled: "Evaluation of LDD MOSFET's Based on Hot-Electron-Induced Degradation", May 1984, pp. 162-165.	

Examiner Signature		Date Considered	
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